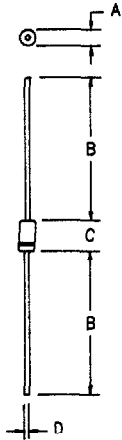


# 8 Amp Schottky Rectifier MS825 - MS845



| Dim. | Inches  |         | Millimeter |         | Notes |
|------|---------|---------|------------|---------|-------|
|      | Minimum | Maximum | Minimum    | Maximum |       |
| A    | .188    | .260    | 4.78       | 6.50    | Dia.  |
| B    | 1.00    | ---     | 25.4       | ---     |       |
| C    | .285    | .375    | 7.24       | 9.52    |       |
| D    | .046    | .056    | 1.17       | 1.42    | Dia.  |

PLASTIC D0201AD

| Microsemi<br>Catalog Number | Working<br>Peak Reverse<br>Voltage | Repetitive<br>Peak Reverse<br>Voltage |  |
|-----------------------------|------------------------------------|---------------------------------------|--|
| MS825                       | 25V                                | 25V                                   | <ul style="list-style-type: none"> <li>• Schottky Barrier Rectifier</li> <li>• Guard Ring Protection</li> <li>• 175°C Junction Temperature</li> <li>• High Current Capability</li> </ul> |
| MS830                       | 30V                                | 30V                                   |  |
| MS835                       | 35V                                | 35V                                   |  |
| MS840                       | 40V                                | 40V                                   |  |
| MS845                       | 45V                                | 45V                                   |  |

| Electrical Characteristics                        |                             |  |
|---|-----------------------------|--|
| Average forward current                           | I <sub>F(AV)</sub> 8.0 Amps | T <sub>A</sub> = 130°C Square wave, R <sub>θJL</sub> = 9.0°C/W, L = 3/8" |
| Maximum surge current                             | I <sub>F(AV)</sub> 400 Amps | 8.3ms, half sine, T <sub>J</sub> = 175°C                                 |
| Max peak forward voltage                          | V <sub>FM</sub> .47 Volts   | I <sub>FM</sub> = 8.0A; T <sub>J</sub> = 150°C *                         |
| Max peak forward voltage                          | V <sub>FM</sub> .62 Volts   | I <sub>FM</sub> = 8.0A; T <sub>J</sub> = 25°C *                          |
| Max peak reverse current                          | I <sub>RM</sub> 250 μA      | V <sub>RRM</sub> , T <sub>J</sub> = 25°C                                 |
| Typical junction capacitance                      | C <sub>J</sub> 660pF        | V <sub>R</sub> = 5.0V, T <sub>J</sub> = 25°C                             |
| * Pulse test: Pulse width 300 μsec, Duty cycle 2% |                             |  |

| Thermal and Mechanical Characteristics |                           |                                 |
|--|---------------------------|---------------------------------|
| Storage temperature range              | T <sub>STG</sub>          | -40°C to 175°C                  |
| Operating junction temp range          | T <sub>J</sub>            | -40°C to 175°C                  |
| Maximum thermal resistance             | L = 3/8" R <sub>θJL</sub> | 9.0°C/W Junction to Lead        |
| Weight                                 |                           | .032 ounces (1.0 grams) typical |

**Microsemi Corp.**  
**Colorado**

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FAX: 303-466-3775

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# MS825 - MS845

Figure 1  
Typical Forward Characteristic

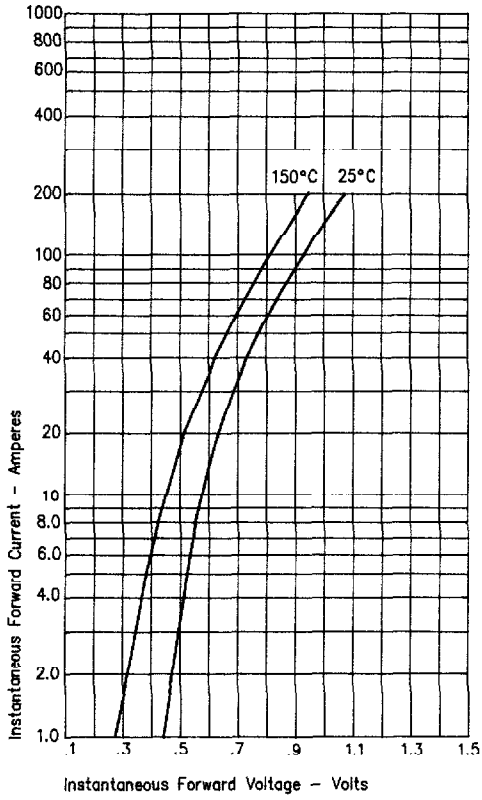


Figure 3  
Typical Junction Capacitance

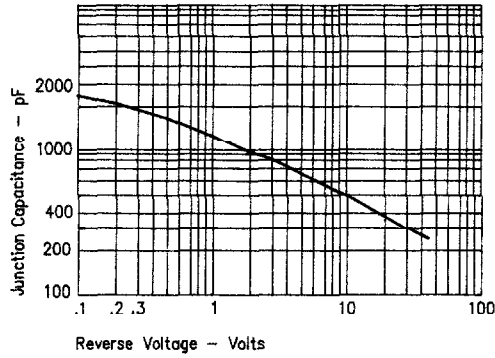


Figure 4  
Forward Current Derating

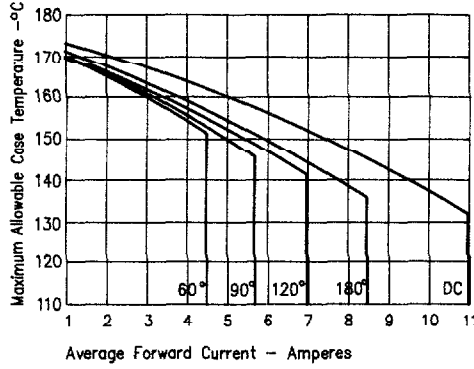


Figure 2  
Typical Reverse Characteristics

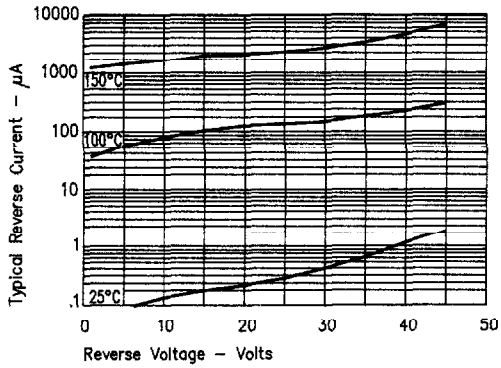


Figure 5  
Maximum Forward Power Dissipation

